74HC2G00-Q100; 74HCT2G00-Q100

Dual 2-input NAND gate Rev. 1 — 7 November 2013

Product data sheet

1. General description

The 74HC2G00-Q100; 74HCT2G00-Q100 is a dual 2-input NAND gate. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

This product has been gualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

Features and benefits 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - For 74HC2G00-Q100: CMOS level
 - For 74HCT2G00-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

Ordering information 3.

Table 1. **Ordering information**

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G00DP-Q100	–40 °C to +125 °C	TSSOP8 plastic thin shrink small outline package;		SOT505-2
74HCT2G00DP-Q100			8 leads; body width 3 mm; lead length 0.5 mm	
74HC2G00DC-Q100	–40 °C to +125 °C	VSSOP8 plastic very thin shrink small outline package;		SOT765-1
74HCT2G00DC-Q100			8 leads; body width 2.3 mm	

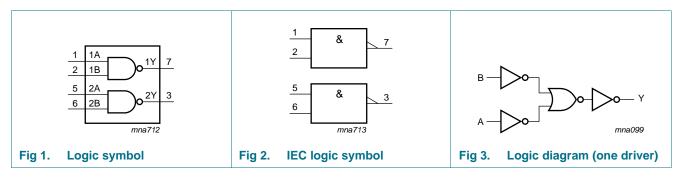


4. Marking

Table 2. Marking code	
Type number	Marking code ^[1]
74HC2G00DP-Q100	H00
74HCT2G00DP-Q100	T00
74HC2G00DC-Q100	H00
74HCT2G00DC-Q100	T00

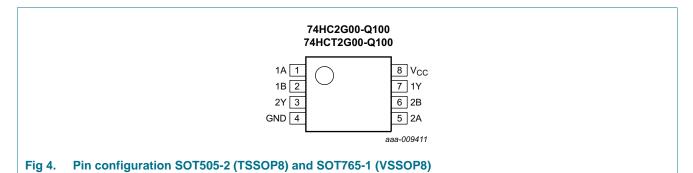
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

Product data sheet

T. I. I. A

7. Functional description

Table 4.	Function table		
Input			Output
nA		nB	nY
L		L	Н
L		Н	Н
Н		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
Ι _{ΟΚ}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _O	output current	$V_{O} = -0.5 \text{ V} \text{ to} (V_{CC} + 0.5 \text{ V})$	<u>[1]</u> _	25	mA
I _{CC}	supply current		<u>[1]</u> _	50	mA
I _{GND}	ground current		<u>[1]</u> –50	-	mA
T _{stg}	storage temperature		-65	+150	°C
PD	dynamic power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	[2] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74H	C2G00-0	Q100	74H	CT2G00-	Q100	Unit	
			Min	Тур	Max	Min	Тур	Max	1	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
VI	input voltage		0	-	V_{CC}	0	-	V _{CC}	V	
Vo	output voltage		0	-	V_{CC}	0	-	V _{CC}	V	
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C	
Δt/ΔV	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V	
	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V	
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V	

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	_40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	
74HC2G0	0-Q100							
	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	V
		I_O = -20 μ A; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		I_O = -4.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
		I_O = -5.2 mA; V_{CC} = 6.0 V	5.63	5.81	-	5.2	-	V
V _{OL}	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	I_{O} = 20 μ A; V_{CC} = 2.0 V	-	0	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±1.0	-	±1.0	μA
I _{CC}	supply current	per input pin; V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	10	-	20	μA
Cı	input capacitance		-	1.5	-	-	-	pF

Dual 2-input NAND gate

Table 7. Static characteristics ... continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	
74HCT2G	00-Q100							
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
VIL	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{OH}	HIGH-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	4.13	4.32	-	3.7	-	V
V _{OL}	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
l _l	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±1.0	-	±1.0	μA
I _{CC}	supply current		-	-	10	-	20	μΑ
ΔI_{CC}	additional supply current	per input; V _{CC} = 4.5 V to 5.5 V; V _I = V _{CC} - 2.1 V; I _O = 0 A	-	-	375	-	410	μA
CI	input capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25$ °C; for test circuit, see <u>Figure 6</u>.

Symbol	Parameter	Conditions		–40 °C to +85 °C		-40 °C t	o +125 °C	Unit	
				Min	Тур	Max	Min	Max	
74HC2G	00-Q100								
t _{pd}	propagation delay	nA and nB to nY; see Figure 5	[1]						
		$V_{CC} = 2.0 V$		-	25	95	-	110	ns
		$V_{CC} = 4.5 V$		-	9	19	-	22	ns
		$V_{CC} = 6.0 V$		-	7	16	-	20	ns
t _t	transition time	see Figure 5	[2]						
		$V_{CC} = 2.0 V$		-	18	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	19	-	25	ns
		$V_{CC} = 6.0 V$		-	5	16	-	20	ns
C _{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	[3]	-	10	-	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25 \text{ °C}$; for test circuit, see Figure 6.

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	–40 °C t	Unit	
				Min	Тур	Max	Min	Max	
74HCT2	G00-Q100								
t _{pd}	propagation delay	nA and nB to nY; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	12	24	-	29	ns
t _t	transition time	$V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 5}}{1000}$	[2]	-	6	19	-	22	ns
C _{PD}	power dissipation capacitance	$V_{\rm I}$ = GND to $V_{\rm CC}$ – 1.5 V	[3]	-	10	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

- [2] t_t is the same as t_{TLH} and t_{THL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms

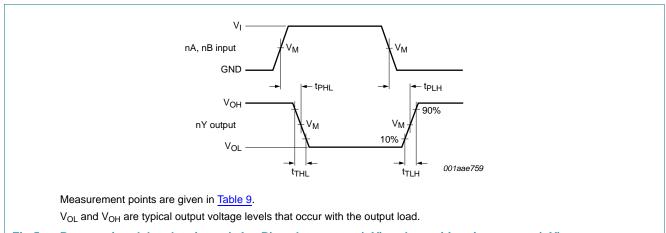


Fig 5. Propagation delay data input (nA, nB) to data output (nY) and transition time output (nY)

Table 9. Measurement points

Туре	Input	Output
	V _M	V _M
74HC2G00-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G00-Q100	1.3 V	1.3 V

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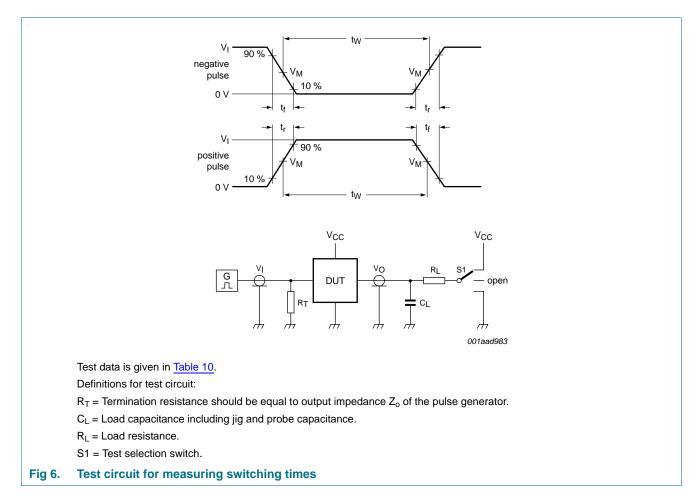


Table 10. Test data

Туре	Input		Load	S1 position	
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}
74HC2G00-Q100	V _{CC}	≤ 6 ns	50 pF	1 kΩ	open
74HCT2G00-Q100	3 V	≤ 6 ns	50 pF	1 kΩ	open

13. Package outline



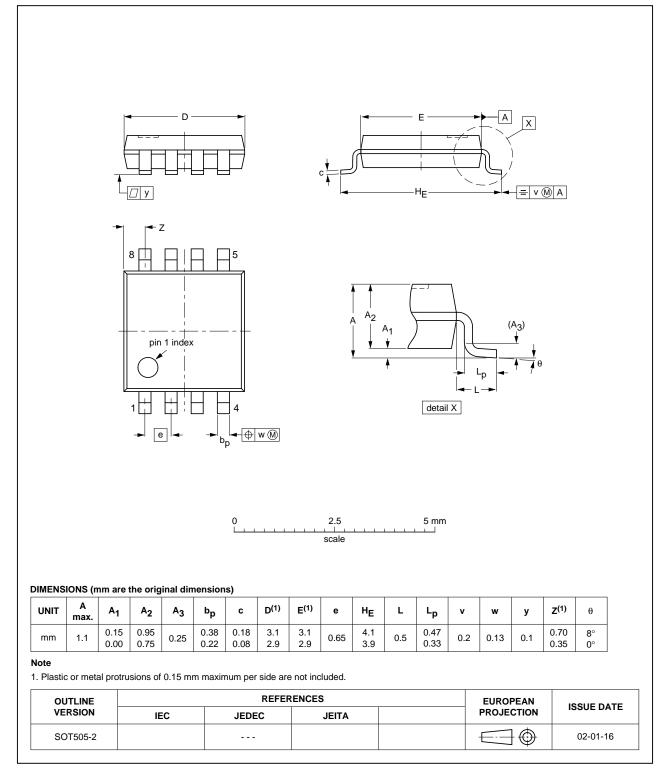


Fig 7. Package outline SOT505-2 (TSSOP8)

74HC_HCT2G00_Q100

74HC2G00-Q100; 74HCT2G00-Q100

Dual 2-input NAND gate

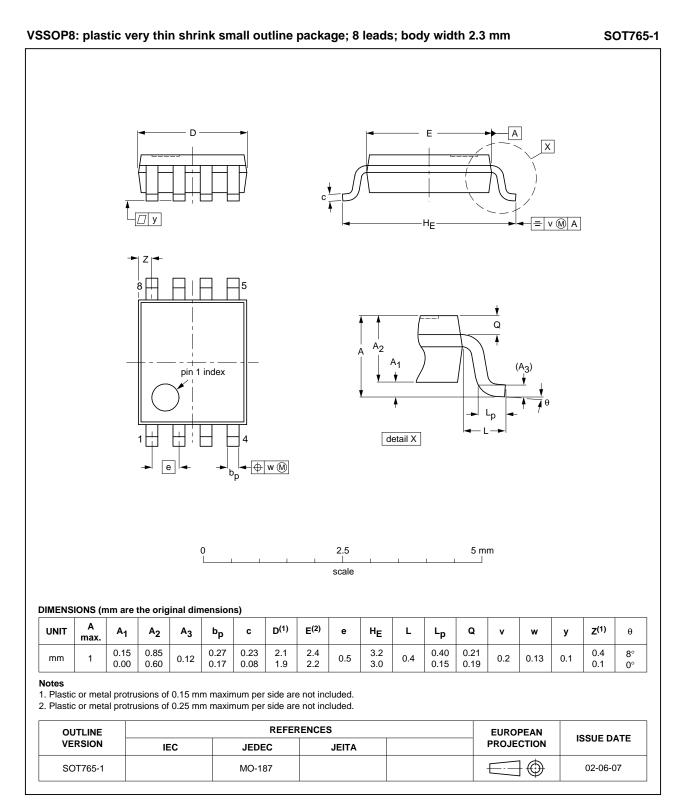


Fig 8. Package outline SOT765-1 (VSSOP8)

74HC_HCT2G00_Q100

14. Abbreviations

Table 11. Abbreviations			
Acronym	Description		
CMOS	Complementary Metal-Oxide Semiconductor		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		
TTL	Transistor-Transistor Logic		

15. Revision history

Table 12.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G00_Q100 v.1	20131107	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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